

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L2	2965	(ru or ruthenium) near20 (substrate or wafer)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2003/07/1 5 19:51	
2	BRS	L1	4	(rough) near (ru or ruthenium) near20 (substrate or wafer)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2003/07/1 5 19:51	

	U	1	PT	P	Document ID	Issue Date	Pages	Title
1	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20020058415 A1	20020516	18	Methods for forming rough ruthenium-containing layers and structures/methods using same
2	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20020058414 A1	20020516	18	Methods for forming rough ruthenium-containing layers and structures/methods using same
3	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6429127 B1	20020806	18	Methods for forming rough ruthenium-containing layers and structures/methods using same
4	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6429127 B	20030205	18	Formation of rough conductive layer used in capacitor structures of memory devices involves heating substrate assembly and passing carrier gas into reaction chamber through ruthenium containing precursor